

Si PIN Photo Diode IP-Si 3252Y

Characteristics:

Large Detection Area

Low Dark Current

High Responsivity

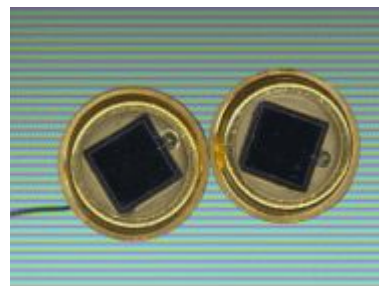
High Reliability

Applications:

Opto-Electronic Target Detection System.

0.4-1.1 μ m Opto-Electronic Detection and

ConveIPion.



Device Mechanism:

Working under reverse bias condition, PIN Device structure.

Technical Parameter(TA=23°C)

Parameter		Symbol	Test Conditions	Typical	Unit
Active Area		Φ		6×6	μm
Optical Parameter	Spectrum Response Range	λ		400~1100	nm
	Responsivity	R_e	$V_R=10\text{mV}$ $\lambda=900\text{nm}$	0.5	A/W
	Response Time	t_r	$V_R=10\text{mV}$	200	nS
Electrical Parameter	Dark Current	I_D	$V_R=10\text{mV}$	700	PA
	Reverse Break Down Voltage	V_{BR}	$I_R=10\mu\text{A}$	20	V
	Capacitance	C_j	$f=1\text{MHz}$ $V_R=10\text{mV}$	280	pF
Operating Voltage		V_R		10	mV
Package			T0-8		
Saturation Power $\leq 0.3\text{w/cm}^2$					

Typical Operating Characteristics:

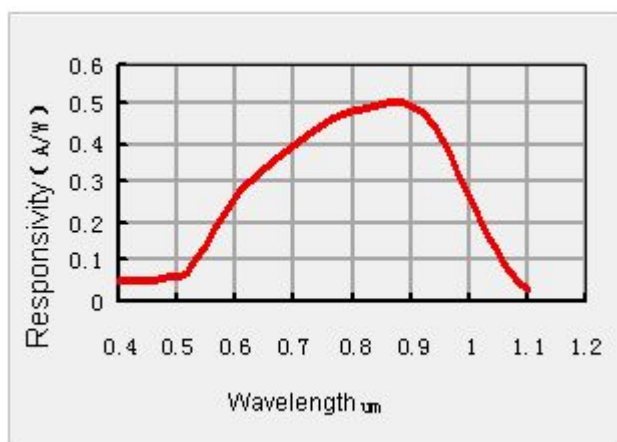


Fig. 1 Spectrum response curve

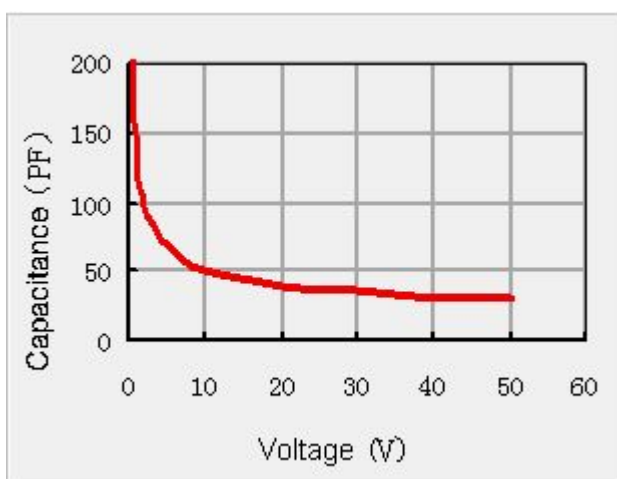
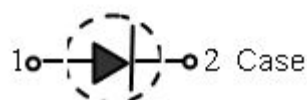
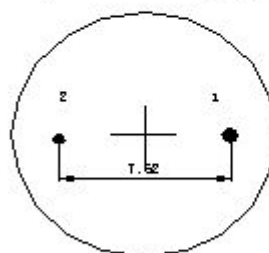
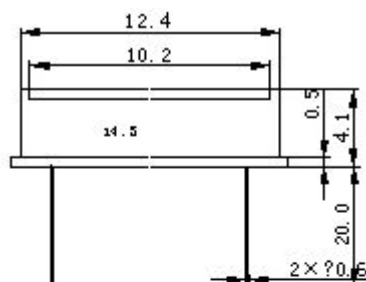


Fig. 2 C-V Curve

Package Information and Usage instruction (Pin Configuration is the back View)



TO-8

Note
 Bias voltage must be less than 10mV
 No Vibration and shock when device operating
 Static Charge Protection (Storage, Operating)